

IN THE SPECIFICATION

Please amend the paragraph beginning at page 65, line 25 and ending on page 66, line 3, with the following rewritten paragraph:

The sense amplifier circuit (sense latch) 13 is constituted of: the same number of sense amplifiers S/Ai, S/Aj as that of the bit lines BLi0, . . . BLi7, BLj0, . . . BLj7; and high ~~withstand pressure voltage~~ transistors M9 for supplying the erase potential Vera to the bit lines BLi0, . . . BLi7, BLj0, . . . BLj7. The high voltage transistor transfers a potential higher than the power potential such as the erase potential.

Please amend the paragraph beginning at page 66, line 18 and ending at line 26, with the following rewritten paragraph:

The high ~~withstand pressure voltage~~ transistors M9 connected to the bit lines BLi0, . . . BLi7 are controlled by the column selection signal CSLi. For example, at the erase time, when the column selection signal CSLi indicates "H", the high ~~withstand pressure voltage~~ transistors M9 connected to the bit lines BLi0, . . . BLi7 are brought into the on state, and the erase potential Vera is supplied to the bit lines BLi0, . . . BLi7.

Please amend the paragraph beginning at page 66, line 27 and ending on page 67, line 8, with the following rewritten paragraph:

The high ~~withstand pressure voltage~~ transistors M9 connected to the bit lines BLj0, . . . BLj7 are controlled by the column selection signal CSLj. For example, at the erase time, when the column selection signal CSLj indicates "H", the high ~~withstand pressure voltage~~

transistors M9 connected to the bit lines BLj0, . . . BLj7 are brought into the on state, and the erase potential Vera is supplied to the bit lines BLj0, . . . BLj7.

Please amend the paragraph beginning at page 68, line 20 and ending at line 25, with the following rewritten paragraph:

It is to be noted that the transistors M1, M9 are constituted of high ~~withstand-pressure~~ voltage transistors so as to be prevented from being destroyed by a high voltage at an erase operation time. The high ~~withstand-pressure-voltage~~ voltage transistor may be either the N channel MOS transistor or P channel MOS transistor.